
Silicon Compatible Materials, Processes, and Technologies for Advanced Integrated Circuits and Emerging Applications 7

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Published by

The Electrochemical Society65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecst*transactions*TM**Vol. 77, No. 5**

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)
ISSN 2151-2051 (cd-rom)

ISBN 978-1-62332-450-6 (CD-ROM)
ISBN 978-1-60768-808-2 (PDF)

Printed in the United States of America.

ECS Transactions, Volume 77, Issue 5

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Table of Contents

<i>Preface</i>	<i>iii</i>
----------------	------------

**Chapter 1
Keynote**

(Invited) VLSI-CMOS Device Technology Scaling Landscape Based on Fully-Depleted SOI and 3D-FinFET Technologies for the Internet of Everything Era <i>J. Hoentschel, R. Carter, B. Rice</i>	3
--	---

**Chapter 2
FEOL Materials and Process Technology**

(Invited) Gate-All-Around Transistors Based on Vertically Stacked Si Nanowires <i>H. Mertens, R. Ritzenhaler, A. Y. Hikavyy, M. S. Kim, Z. Tao, K. Wostyn, T. Schram, E. Kunnen, L. Å. Ragnarsson, H. F. W. Dekkers, T. Hopf, K. Devriendt, D. Tsvetanova, S. A. Chew, Y. Kikuchi, E. Van Besien, E. Rosseel, G. Mannaert, A. De Keersgieter, A. Chasin, S. Kubicek, A. Dangol, S. Demuynck, K. Barla, D. Mocuta, N. Horiguchi</i>	19
(Invited) Challenges for Ion Implantation in Power Device Processing <i>W. Schustereder</i>	31
The Effect of Defects on Time Dependent Dielectric Breakdown Acceleration in TiN/ZrO ₂ /Al ₂ O ₃ /p-Ge Gate Stacks <i>Y. Ding, D. Misra, K. Tapily, R. D. Clark, S. Consiglio, C. S. Wajda, G. J. Leusink</i>	43
Argon Annealed ALD-ZrO ₂ /SiON Gate Stack for Advanced CMOS Devices <i>R. Gupta, D. Saikia, R. Vaid</i>	51

Chapter 3 Contact and MOL Technology

(Invited) Contacts in Advanced CMOS: History and Emerging Challenges <i>C. Lavoie, P. Adusumilli, A. V. Carr, J. S. Jordan Sweet, A. S. Ozcan, E. Levrau, N. Breil, E. Alptekin</i>	59
MIS(p) Saturation Tunneling Current Controlled by Neighboring MIS Inversion Level Via Coupling Effect <i>M. H. Yang, J. G. Hwu</i>	81
Cobalt CMP Development for 7nm Logic Device <i>C. Wu, J. H. Han, X. Shi, D. R. Koli, D. Penigalapati</i>	93
Rearrangement of Fringing Field by Sidewall Passivated Metal Gate in MIS Tunnel Diode <i>C. J. Chou, J. G. Hwu</i>	99

Chapter 4 BEOL Material and Process Technology

Low Hydrogen Silicon Carbon Nitride Cap for High Performance Sub-10 nm Cu-Low k Interconnect <i>S. V. Nguyen, H. K. Shobha, T. J. Haigh, Y. Yao, L. Tai, S. A. Cohen, T. M. Shaw, C. K. Hu, E. Liniger, K. Virwani, A. J. Kellock, D. F. Canaperi</i>	111
Modeling and Simulation of Cu Diffusion in Porous Low-k Dielectrics <i>R. Ali, Y. Fan, S. W. King, M. K. Orlowski</i>	121
Study of Seed-Layer Stability on Copper Electrolytic Bath <i>E. Delbos, I. Setoain, M. Frégnaux, A. M. Gonçalves, A. Etcheberry</i>	133
Investigation of Thermal Treatment Processes for Dissimilar Wafer Bonding <i>C. Wang, Y. Li, Y. Liu, Z. Yuan, Y. Tian, C. Wang, T. Suga</i>	143
Incorporation of the Organic Additives during the Damascene or TSV Process: Influence of the Applied Waveform <i>E. Delbos, F. Jomard, M. Bouttemy, A. Etcheberry</i>	153

Chapter 5

Gordon E. Moore Medal for Outstanding Achievement in Solid State Science and Technology Award

(Gordon E. Moore Medal for Outstanding Achievement in Solid State Science and Technology Address) Transient Polymers for Low-k Dielectrics and Vaporizing Devices

P. A. Kohl

165

Chapter 6

New Materials and Device Architectures

(Invited) Bringing III-Vs into CMOS: From Materials to Circuits
L. Czernomaz, V. V. Deshpande, E. O'Connor, D. Caimi, M. Sousa, J. Fompeyrine

173

(Invited) 2D/3D Tunnel-FET: Toward Green Transistors and Sensors
W. Cao, J. Kang, K. Banerjee

185

The Virtual Diode with Electrostatic Doping
K. Lee, M. Bawedin, M. Parihar, H. J. Park, S. Cristoloveanu

191

Chapter 7

Materials and Processes for Silicon Technology

Controlled Fabrication of High-Aspect-Ratio Microstructures in Silicon at Etching Rates Beyond State-of-the-Art Microstructuring Technologies
C. Cozzi, G. Polito, K. W. Kolasinski, G. Barillaro

199

Electrolyzed Sulfuric Acid Application in Semiconductor Cleaning Processes:
An Advanced Substitution of SPM Cleaning
J. H. Ahn, P. D. Kim, S. C. Hwang, J. Seo, S. Lee, Y. Ogawa, J. Ida, Y. Sasaki, T. Nagai, T. Otsu

207

Hydrogen-Induced Crystallization of Germanium Films at Low Temperature Using an RF-PECVD Reactor
G. Dushaq, M. Rasras, A. Nayfeh

213

Ultra-High Purity Hydrazine Delivery for Low Temperature Metal Nitride ALD
D. Alvarez Jr., J. Spiegelman, R. Holmes, K. Andachi, M. Raynor, H. Shimizu

219

The Role of Polysilicon Slurry and Its Application in 7nm CMP <i>T. F. Chao, D. Penigalapati, J. C. Yang, H. Huang, D. R. Koli</i>	227
Multi-Wavelength Raman Characterization of Epitaxial Silicon Wafers for In-Line Process Characterization and Monitoring Applications <i>W. S. Yoo, T. Ishigaki, K. Kang</i>	235
Chapter 8 Poster Session	
Thermal Budget Reduction in Triple Gate Oxide Process by Wet Etch Technique <i>H. Tai, H. Y. Liao, H. A. Chen, P. T. Tou, W. T. Liu, M. C. Lu, T. H. Ying</i>	245
Enhancement of Light-to-Dark Current Ratio Via Coupling Effect for MIS (p) Tunnel Diode Photo Sensors <i>W. T. Hou, W. C. Kao, J. G. Hwu</i>	249
Controlling the Electrochemical Etching of Pores with High Aspect Ratio at the Submicrometer Scale in Silicon <i>G. Polito, C. Cozzi, G. Barillaro</i>	259
Author Index	267